

Description

The IRLML2030TRPBF uses advanced trench technology

to provide excellent $R_{\text{DS}(\text{ON})},$ low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

General Features

V_{DS} = 30V I_D =5.8A

 $R_{DS(ON)} < 30m\Omega @ V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply

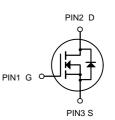
Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
IRLML2030TRPBF	SOT-23	A09T XXXX	3000

Absolute Maximum Ratings (T_A=25[°]C unless otherwise noted)

Symbol	Parameter	Limit	Unit
Vds	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±12	V
lo	Drain Current-Continuous	5.8	A
Ырм	Drain Current-Pulsed (Note 1)	30	A
PD	Maximum Power Dissipation	1.4	W
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	89	°C/W





N-Channel MOSFET



N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_A=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Мах	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	30	33	-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =30V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	lgss	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	$V_{DS}=V_{GS}$, $I_D=250\mu A$	0.7	0.9	1.4	V
	Rds(on)	V _{GS} =2.5V, I _D =4A	-	41	55	mΩ
Drain-Source On-State Resistance		V _{GS} =4.5V, I _D =5A	-	32	42	mΩ
		V _{GS} =10V, I _D =5.8A	-	28	30	mΩ
Forward Transconductance	gfs	V _{DS} =5V,I _D =5A	10	-	-	S
Input Capacitance	Clss		-	825	-	PF
Output Capacitance	Coss	V _{DS} =15V,V _{GS} =0V,	-	100	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	78	-	PF
Turn-on Delay Time	td(on)		-	3.3	-	nS
Turn-on Rise Time	tr	V _{DD} =15V, RL=2.7Ω	-	4.8	-	nS
Turn-Off Delay Time	td(off)	V_{GS} =10V, R_{GEN} =3 Ω	-	26	-	nS
Turn-Off Fall Time	t _f		-	4	-	nS
Total Gate Charge	Qg		-	10	-	nC
Gate-Source Charge	Qgs	V _{DS} =15V,I _D =5.8A,	-	1.6	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =4.5V	-	3.1	-	nC
Diode Forward Voltage (Note 3)	Vsd	V _{GS} =0V,I _S =5.8A	-	-	1.2	V
Diode Forward Current (Note 2)	ls		-	-	5.8	Α

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

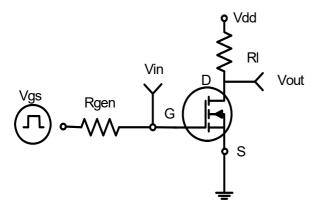
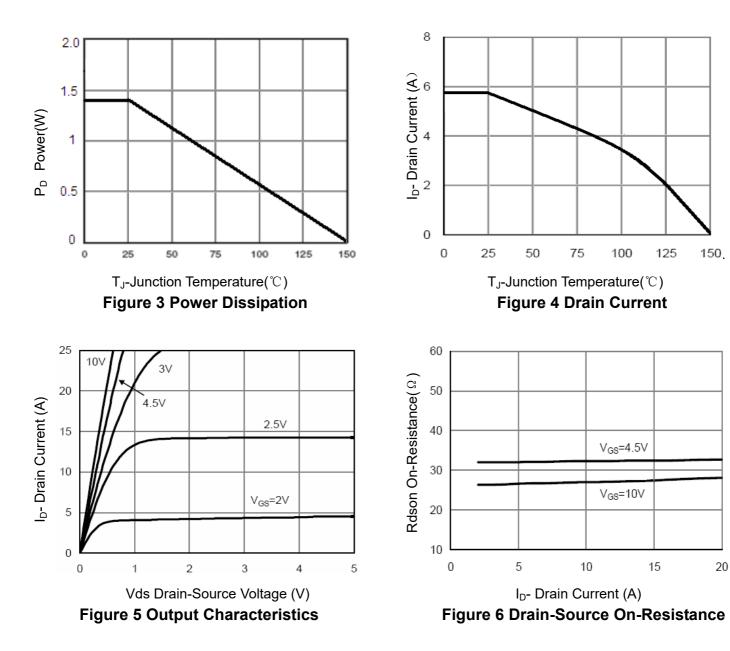
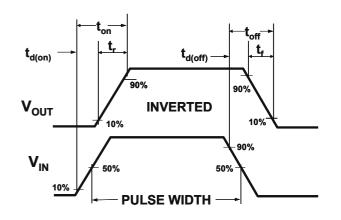
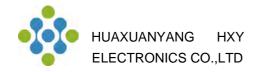


Figure 1:Switching Test Circuit



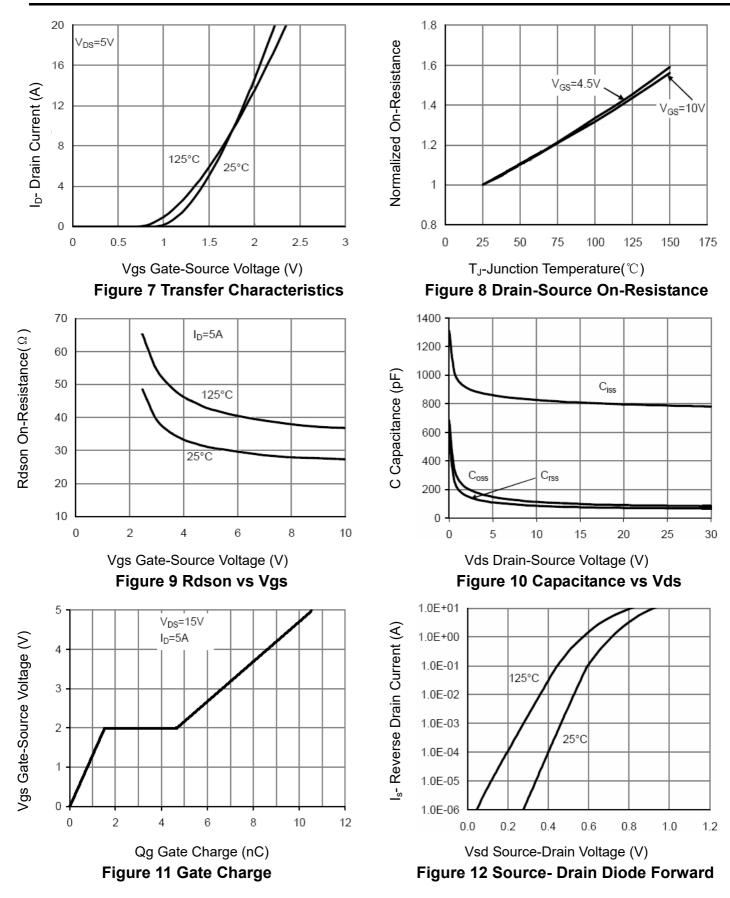






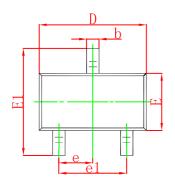
IRLML2030TRPBF

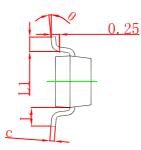
N-Channel Enhancement Mode MOSFET

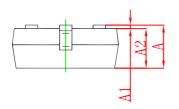




SOT-23 Package Outline Dimensions

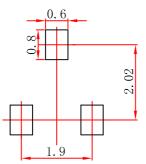






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
e	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



Note: 1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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